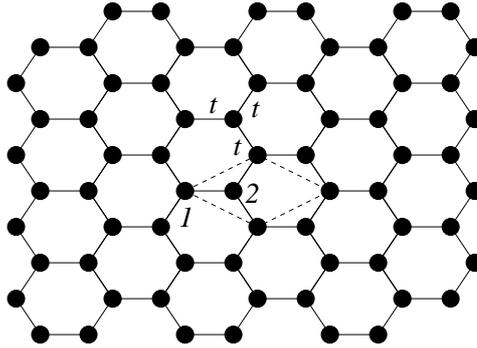


Problem set #9

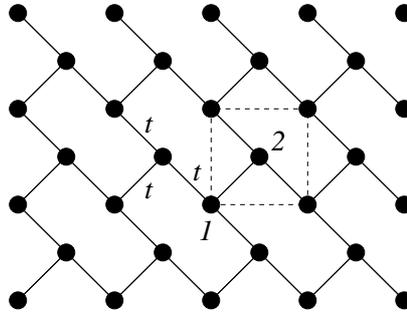
1. Band structure for graphene – tight binding model:

Carbon atoms in graphene form a 2D hexagonal lattice.



Note that there are two atoms per unit cell. We assume that electrons can only hop to the nearest neighbor atoms. The hopping amplitude is t .

To find the band structure of graphene as described by the tight binding model, let us deform the hexagonal lattice to a square lattice



For the square lattice, we can use $|\mathbf{i}, 1\rangle$ and $|\mathbf{i}, 2\rangle$ to represent the states on the Carbon atoms, where

$$\mathbf{i} = n_1\mathbf{x} + n_2\mathbf{y}, \quad n_1, n_2 = \text{integers.}$$

The hopping Hamiltonian for a single electron can now be written as

$$H = t \sum_{\mathbf{i}} (|\mathbf{i}, 1\rangle\langle\mathbf{i}, 2| + |\mathbf{i}, 2\rangle\langle\mathbf{i}, 1|) + t \sum_{\mathbf{i}} (|\mathbf{i} + \mathbf{x}, 1\rangle\langle\mathbf{i}, 2| + |\mathbf{i}, 2\rangle\langle\mathbf{i} + \mathbf{x}, 1|) \\ + t \sum_{\mathbf{i}} (|\mathbf{i} + \mathbf{y}, 1\rangle\langle\mathbf{i}, 2| + |\mathbf{i}, 2\rangle\langle\mathbf{i} + \mathbf{y}, 1|)$$

The three terms represent the the hopping through the three different types of links.

- (a) Write the hopping Hamiltonian in the form

$$H = \sum_{\mathbf{i}, a, b} |\mathbf{i}, b\rangle M_{ba}^0 \langle \mathbf{i}, a| + \sum_{\mathbf{i}, a, b} (|\mathbf{i} + \mathbf{x}, b\rangle M_{ba}^1 \langle \mathbf{i}, a| + h.c.) + \sum_{\mathbf{i}, a, b} (|\mathbf{i} + \mathbf{y}, b\rangle M_{ba}^2 \langle \mathbf{i}, a| + h.c.)$$

and find the 2 by 2 matrices M^0 , M^1 and M^2 . (Hint: note that $(\hat{O} + h.c.) \equiv \hat{O} + \hat{O}^\dagger$.)

- (b) Assume that the square lattice has a size $L \times L$ (the lattice constant is assumed to be $a = 1$) and has a periodic boundary condition in both x - and y -directions. Let

$$|\mathbf{k}, a\rangle = L^{-1} \sum_{\mathbf{i}} e^{i\mathbf{k}\cdot\mathbf{i}} |\mathbf{i}, a\rangle$$

be the plane-wave states that satisfy the periodic boundary condition. Find the quantization condition on \mathbf{k} . Find the range of \mathbf{k} so that different \mathbf{k} 's in that range will correspond to different states. Show that in terms of the plane-wave states, the hopping Hamiltonian can be rewritten as

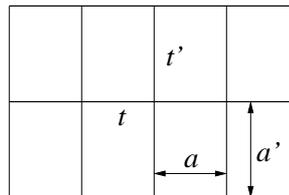
$$H = \sum_{\mathbf{k}, a, b} |\mathbf{k}, b\rangle M_{ba}(\mathbf{k}) \langle \mathbf{k}, a|$$

Find the 2 by 2 matrix $M(\mathbf{k})$.

- (c) From the 2 by 2 matrix $M(\mathbf{k})$, calculate the dispersions of the two bands $\epsilon_1(\mathbf{k})$ and $\epsilon_2(\mathbf{k})$. Plot the dispersions. Find the locations in the Brillouin zone where the two band touches, ie $\epsilon_1(\mathbf{k}) = \epsilon_2(\mathbf{k})$.

2. Conductivity of a semiconductor with rectangular lattice

Atoms in a semiconductor form a rectangular lattice. We assume that electrons can only hop to the nearest neighbor atoms. The hopping amplitude is t in the x -direction and t' in the y -direction. The lattice constant is a in the x -direction and a' in the y -direction.



- (a) Find the dispersion $\epsilon(\mathbf{k})$ of the tight binding band.
 (b) Find the mass matrix $(m^{-1})_{ij}$ that describes the mass of an electron near the bottom of the band. (Hint: Near the bottom of band located at \mathbf{k}_0 , $\epsilon(\mathbf{k}_0 + \mathbf{k})$ has a form

$$\epsilon(\mathbf{k}_0 + \mathbf{k}) = \frac{1}{2} \sum_{ij} (m^{-1})_{ij} k_i k_j + \text{const.}$$

for small \mathbf{k} .)

- (c) Use the Drude model to calculate the conductivity tensor σ_{ij} . Here we assume that the band is occupied by a dilute gas of electrons (ie the electron density $n \ll 1/aa'$) and the

relaxation time is τ . Note that at low temperatures the electrons are near the bottom of the band. (Hint: the equation of motion is given by

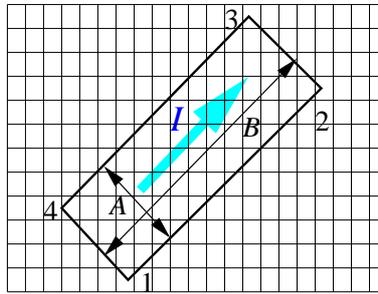
$$\frac{dv_i}{dt} = \sum_j (m^{-1})_{ij} F_j - \frac{1}{\tau} v_i$$

where \mathbf{v} is the velocity of the electrons and \mathbf{F} is the force that acts on an electron. The conductivity tensor σ_{ij} is defined through

$$J_i = \sum_j \sigma_{ij} E_j$$

where \mathbf{J} is the electric current density induced by an electric field \mathbf{E} .)

- (d) Find the resistivity tensor defined through $E_i = \sum_j \rho_{ij} J_j$.
 (e) A rectangular stripe of the 2D crystal is cut as shown in the figure below.



The angle between the edge of the stripe and x -direction is 45° . The size of the stripe is $A \times B$. If we pass a current I through the stripe, what is the voltage drop between the corner 1 and the corner 2? What is the voltage drop between the corner 1 and the corner 4?

3. Prob. 2 on page 218 of Kittel.